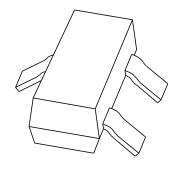
DISCRETE SEMICONDUCTORS

DATA SHEET



BAV170 Low-leakage double diode

Product specification Supersedes data of June 1994 File under Discrete Semiconductors, SC01 1996 Mar 13





Low-leakage double diode

BAV170

FEATURES

- Plastic SMD package
- Low leakage current: typ. 3 pA
- Switching time: typ. 0.8 μs
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

APPLICATION

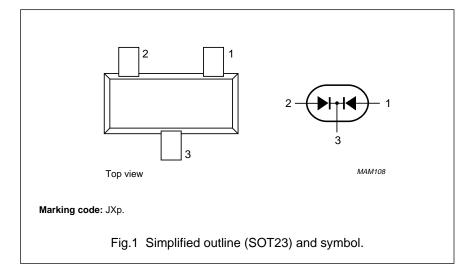
• Low-leakage current applications in surface mounted circuits.

DESCRIPTION

Epitaxial, medium-speed switching, double diode in a small plastic SOT23 SMD package. The diodes are in common cathode configuration.

PINNING

PIN	DESCRIPTION
1	anode
2	anode
3	common cathode



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode	Per diode				
V _{RRM}	repetitive peak reverse voltage		_	85	V
V _R	continuous reverse voltage		_	75	V
I _F	continuous forward current	single diode loaded; see Fig.2; note 1	_	215	mA
		double diode loaded; see Fig.2; note 1	-	125	mA
I _{FRM}	repetitive peak forward current		_	500	mA
I _{FSM}	non-repetitive peak forward current	square wave; $T_j = 25$ °C prior to surge; see Fig.4			
		$t_p = 1 \mu s$	_	4	Α
		t _p = 1 ms	_	1	Α
		t _p = 1 s	_	0.5	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 1	1	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C

Note

1. Device mounted on a FR4 printed-circuit board.

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ELECTRICAL CHARACTERISTICS

 $T_i = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					•
V _F	forward voltage	see Fig.3			
		I _F = 1 mA	_	900	mV
		I _F = 10 mA	_	1000	mV
		I _F = 50 mA	_	1100	mV
		I _F = 150 mA	_	1250	mV
I _R	reverse current	see Fig.5			
		V _R = 75 V	0.003	5	nA
		V _R = 75 V; T _j = 150 °C	3	80	nA
C _d	diode capacitance	f = 1 MHz; V _R = 0; see Fig.6	2	_	pF
t _{rr}	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 10$ mA; $R_L = 100$ Ω ; measured at $I_R = 1$ mA; see Fig.7	0.8	3	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		360	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	500	K/W

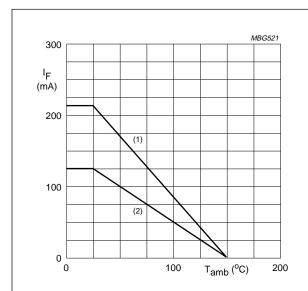
Note

1. Device mounted on a FR4 printed-circuit board.

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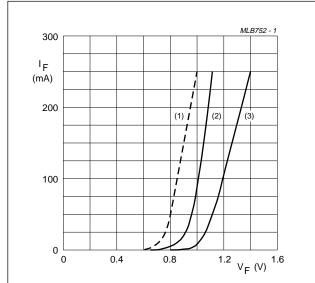
GRAPHICAL DATA



Device mounted on a FR4 printed-circuit board.

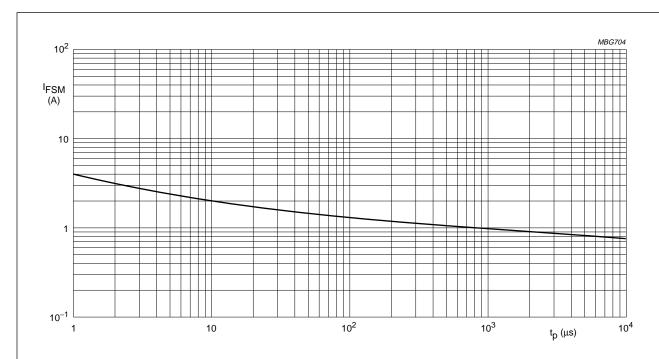
- (1) Single diode loaded.
- (2) Double diode loaded.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



- (1) $T_j = 150 \,^{\circ}\text{C}$; typical values.
- (2) $T_i = 25$ °C; typical values.
- (3) $T_j = 25$ °C; maximum values.

Fig.3 Forward current as a function of forward voltage; per diode.

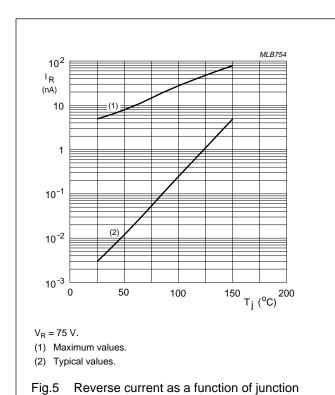


Based on square wave currents; $T_j = 25$ °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration per diode.

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temperature; per diode.

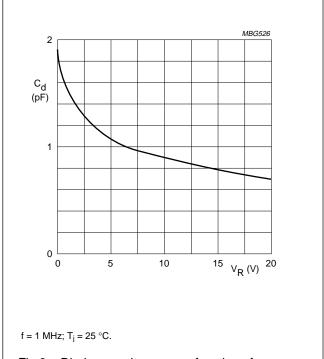
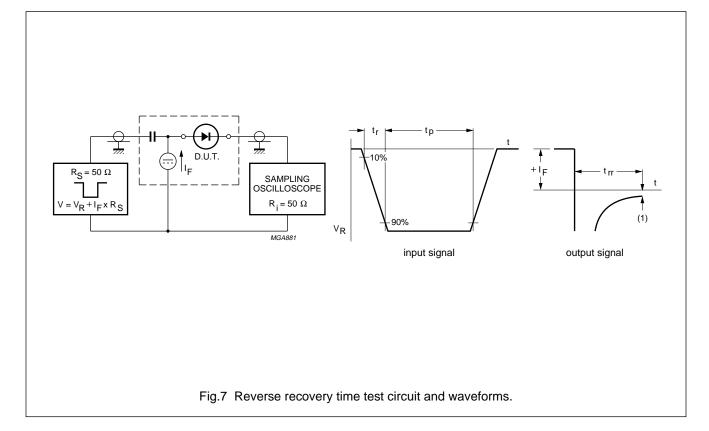


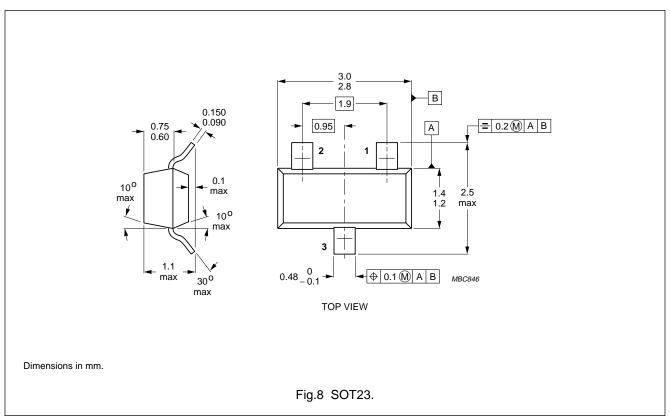
Fig.6 Diode capacitance as a function of reverse voltage; per diode; typical values.



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PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status		
Objective specification	This data sheet contains target or goal specifications for product development.	
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.	
Product specification	This data sheet contains final product specifications.	
Limiting values		
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.		
Application information		
Where application information is given, it is advisory and does not form part of the specification.		

LIFE SUPPORT APPLICATIONS

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